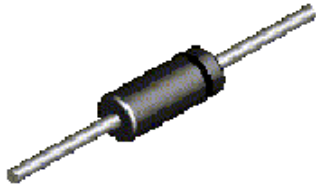


# 1N/FDLL 914/A/B / 916/A/B / 4148 / 4448



DO-35



LL-34

THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

**COLOR BAND MARKING**

DEVICE	1ST BAND	2ND BAND
FDLL914	BLACK	BROWN
FDLL914A	BLACK	GRAY
FDLL914B	BROWN	BLACK
FDLL916	BLACK	RED
FDLL916A	BLACK	WHITE
FDLL916B	BROWN	BROWN
FDLL4148	BLACK	BROWN
FDLL4448	BROWN	BLACK

## Small Signal Diode

### Absolute Maximum Ratings\*

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage	100	V
I <sub>F(AV)</sub>	Average Rectified Forward Current	200	mA
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0	A
		4.0	A
T <sub>stg</sub>	Storage Temperature Range	-65 to +200	°C
T <sub>J</sub>	Operating Junction Temperature	175	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

Symbol	Characteristic	Max	Units
		1N/FDLL 914/A/B / 4148 / 4448	
P <sub>D</sub>	Power Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	300	°C/W

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448

# Small Signal Diode

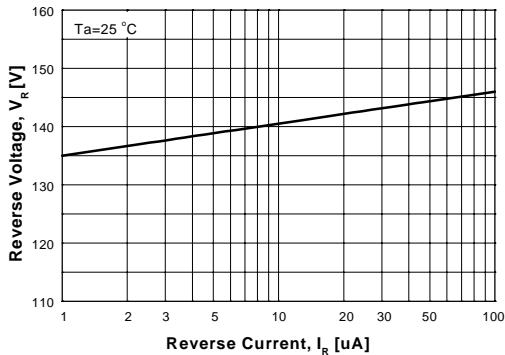
(continued)

## Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise noted

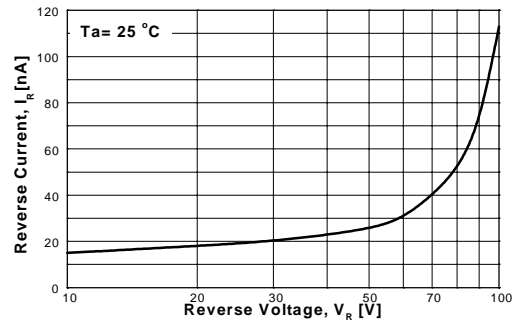
Symbol	Parameter	Test Conditions	Min	Max	Units
V <sub>R</sub>	Breakdown Voltage	I <sub>R</sub> = 100 μA I <sub>R</sub> = 5.0 μA	100 75		V V
V <sub>F</sub>	Forward Voltage	1N914B/4448 I <sub>F</sub> = 5.0 mA 1N916B I <sub>F</sub> = 5.0 mA 1N914/916/4148 I <sub>F</sub> = 10 mA 1N914A/916A I <sub>F</sub> = 20 mA 1N916B I <sub>F</sub> = 20 mA 1N914B/4448 I <sub>F</sub> = 100 mA	620 630	720 730 1.0 1.0 1.0 1.0	mV mV V V V V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 20 V V <sub>R</sub> = 20 V, T <sub>A</sub> = 150°C V <sub>R</sub> = 75 V		25 50 5.0	nA μA μA
C <sub>T</sub>	Total Capacitance	1N916A/B/4448 V <sub>R</sub> = 0, f = 1.0 MHz 1N914A/B/4148 V <sub>R</sub> = 0, f = 1.0 MHz		2.0 4.0	pF pF
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 10 mA, V <sub>R</sub> = 6.0 V (60mA), I <sub>rr</sub> = 1.0 mA, R <sub>L</sub> = 100Ω		4.0	ns

1N/FD/L 914/A/B / 916/A/B / 4148 / 4448

## Typical Characteristics

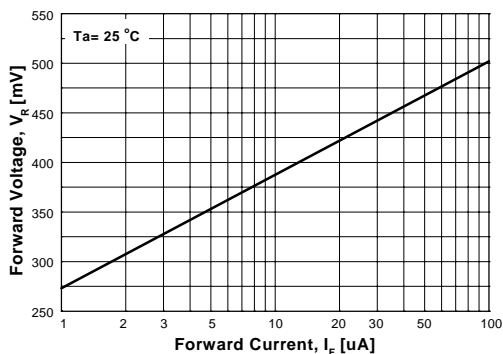


**Figure 1. Reverse Voltage vs Reverse Current**  
BV - 1.0 to 100 uA

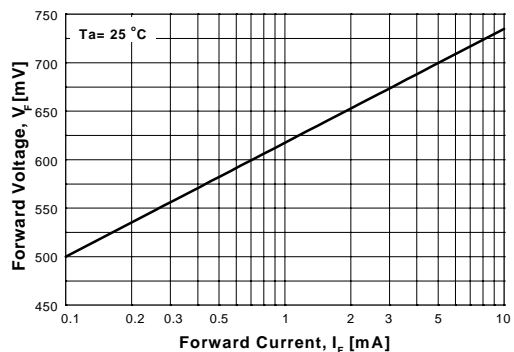


**Figure 2. Reverse Current vs Reverse Voltage**  
IR - 10 to 100 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature



**Figure 3. Forward Voltage vs Forward Current**  
VF - 1 to 100 uA



**Figure 4. Forward Voltage vs Forward Current**  
VF - 0.1 to 10 mA

Typical Characteristics (continued)

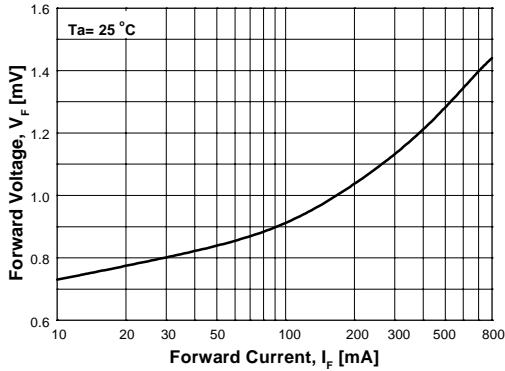


Figure 5. Forward Voltage vs Forward Current  
VF - 10 to 800 mA

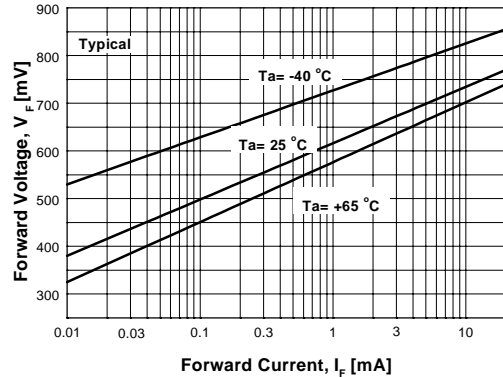


Figure 6. Forward Voltage  
vs Ambient Temperature  
VF - 0.01 - 20 mA (-40 to +65 Deg C)

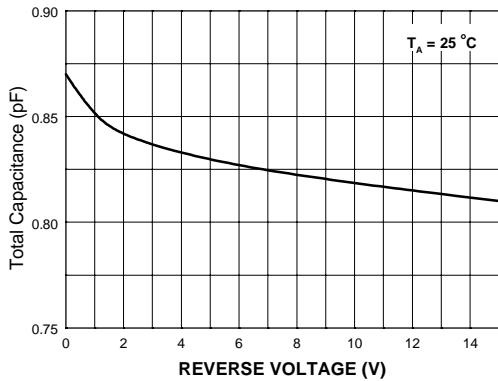


Figure 7. Total Capacitance

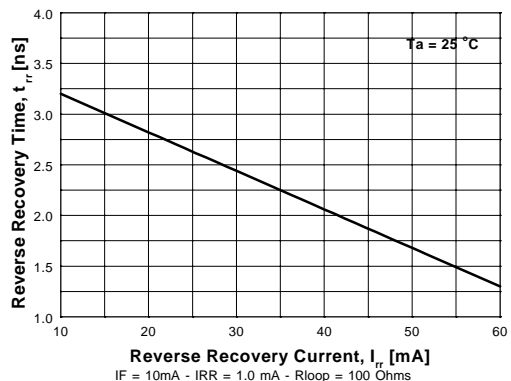


Figure 8. Reverse Recovery Time vs  
Reverse Recovery Current

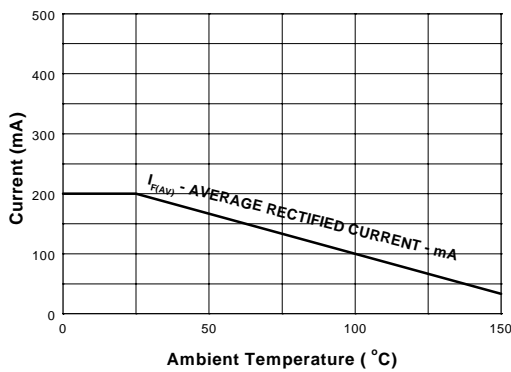


Figure 9. Average Rectified Current ( $I_{F(AV)}$ )  
versus Ambient Temperature ( $T_A$ )

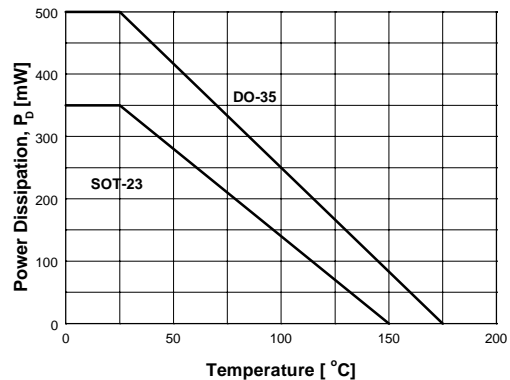


Figure 10. Power Derating Curve